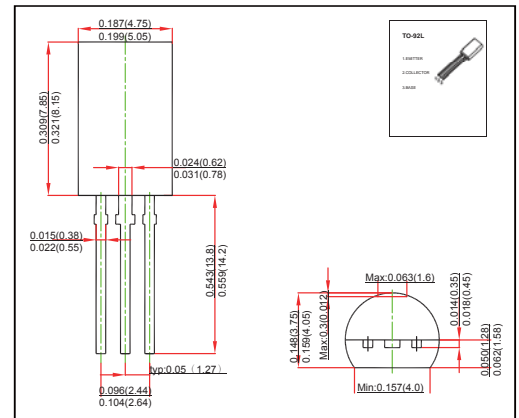


**TO-92L Plastic-Encapsulate Transistors**
**FEATURE**

- High Voltage :V<sub>CEO</sub>=300V
- Small Collector Output Capacitance: Cob=3.0pF(Typ)
- TRANSISTOR (NPN)

**MECHANICAL DATA**

- Case style:TO-92L molded plastic
- Mounting position:any


**MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	300	V
Collector-Emitter Voltage	V <sub>CEO</sub>	300	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Collector Current -Continuous	I <sub>C</sub>	0.1	A
Collector Power Dissipation	P <sub>C</sub>	0.9	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55~+150	°C

**ELECTRICAL CHARACTERISTICS** T<sub>A</sub> =25 °C unless otherwise specified

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR) <sub>CBO</sub>	I <sub>C</sub> = 100μA, I <sub>E</sub> =0	300			V
Collector-emitter breakdown voltage	V(BR) <sub>CEO</sub>	I <sub>C</sub> = 3mA, I <sub>B</sub> =0	300			V
Emitter-base breakdown voltage	V(BR) <sub>EBO</sub>	I <sub>E</sub> = 100μA, I <sub>C</sub> =0	7			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =240V, I <sub>E</sub> =0			1.0	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CB</sub> =240V, I <sub>B</sub> =0			5.0	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 7V, I <sub>C</sub> =0			1.0	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =20mA	30		150	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			1.0	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			1.0	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =20mA, f=30MHz	50			MHz
Collector output capacitance	Cob	V <sub>CB</sub> =20V, I <sub>E</sub> =0, f=1MHz		3		pF